

APD260

#### **Features**

- Low Forward Voltage Drop
- Very Small Conduction Losses
- High Surge Capability
- Surge Overload Rating up to 50A Peak Value

#### **Applications**

- Low Voltage High Frequency Inverters
- DC-DC Converters
- Free Wheeling
- Polarity Protection

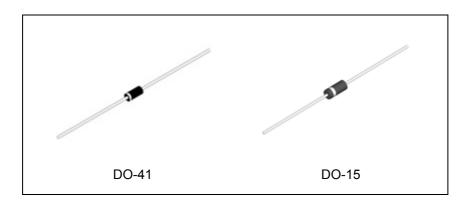


Figure 1. Package Types of APD260

# **Pin Configuration**

VD/VG Package
(DO-41/DO-15)

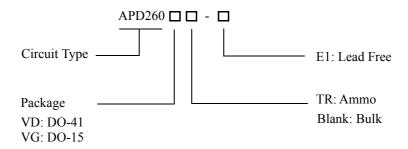
Cathod Anode

Figure 2. Pin Configuration of APD260



APD260

#### **Ordering Information**



Package	Part Number	Marking ID	Packing Type
DO-41	APD260VD-E1	D260VD	Bulk
	APD260VDTR-E1	D260VD	Ammo
DO-15	APD260VG-E1	D260VG	Bulk
	APD260VGTR-E1	D260VG	Ammo

BCD Semiconductor's Pb-free products, as designated with "E1" suffix in the part number, are RoHS compliant.

# **Absolute Maximum Ratings** ( $T_A$ =25°C, unless otherwise noted) (Note 1)

Parameter	Symbol	Value	Unit
Maximum Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	60	V
Maximum DC Blocking Voltage	V <sub>DC</sub>	60	V
Maximum RMS Voltage	V <sub>RMS</sub>	42	V
Average Rectified Forward Current 0.375 " (9.5mm) Lead Length (See Figure 3)	I <sub>F(AV)</sub>	2.0	A
Non-Repetitive Peak Forward Surge Current 8.3 ms Single Half Sine-Wave on Rated Load	I <sub>FSM</sub>	50	A
Operating Junction Temperature Range	$T_{J}$	-65 to 125	°C
Storage Temperature Range	T <sub>STG</sub>	-65 to 150	°C

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.



APD260

# Thermal Characteristics (T<sub>A</sub>=25°C, unless otherwise noted)

Parameter	Symbol	Values	Unit
Typical Thermal Resistance (Note 2)	$R_{ heta JA}$	52	°C/W
Typioni Thermal Telephanie (1, 100 2)	$R_{ heta JL}$	14	C/ W

Note 2: Thermal resistance from junction to lead, PCB mounted, 0.375" (9.5mm) lead length.

# $\textbf{Electrical Characteristics} \; (T_A \!\!=\!\! 25^oC, \, unless \; otherwise \; noted)$

Parameter		Symbol	Values	Unit
Forward Voltage @ I <sub>F</sub> =2.0A		$V_{\mathrm{F}}$	0.68	V
Reverse Current @ Rated V <sub>R</sub> (Note 3)	T <sub>A</sub> =25°C	I <sub>R</sub>	0.5	. mA
K ( ······)	$T_{A}=100^{o}C$		10	

Note 3: Pulse Test: 300 μS pulse width, 1.0% duty cycle.

# **Typical Performance Characteristics** (T<sub>A</sub>=25°C, unless otherwise noted)

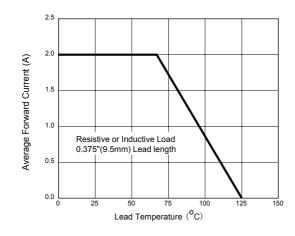


Figure 3. Forward Current Derating Curve

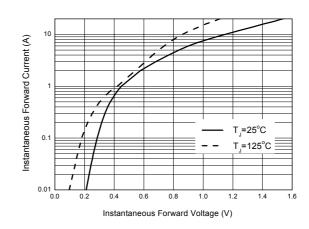
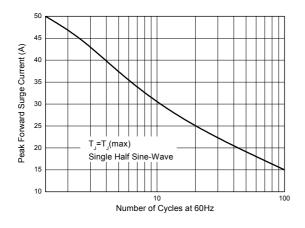


Figure 4. Typical Instantaneous Forward Characteristics

**APD260** 

# **Typical Performance Characteristics (Continued)**



T = 25°C - T = 125°C - T = 125

Figure 5. Maximum Non-Repetitive Peak Forward Surge Current

Figure 6. Typical Reverse Characteristics

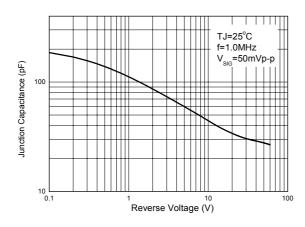


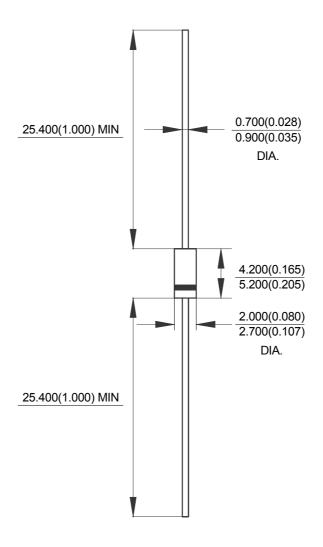
Figure 7. Typical Junction Capacitance



APD260

#### **Mechanical Dimensions**

DO-41 Unit: mm(inch)

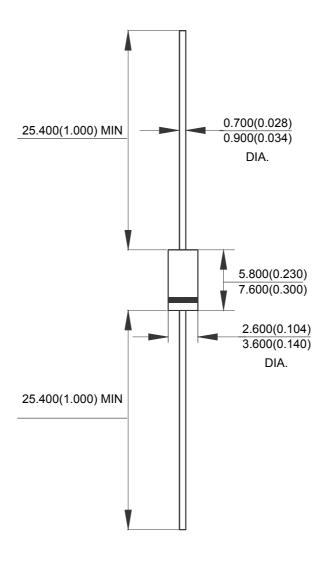




**APD260** 

# **Mechanical Dimensions (Continued)**

DO-15 Unit: mm(inch)







#### **BCD Semiconductor Manufacturing Limited**

http://www.bcdsemi.com

#### IMPORTANT NOTICE

BCD Semiconductor Manufacturing Limited reserves the right to make changes without further notice to any products or specifications herein. BCD Semiconductor Manufacturing Limited does not assume any responsibility for use of any its products for any particular purpose, nor does BCD Semiconductor Manufacturing Limited assume any liability arising out of the application or use of any its products or circuits. BCD Semiconductor Manufacturing Limited does not convey any license under its patent rights or other rights nor the rights of others.

#### MAIN SITE

- Headquarters

BCD Semiconductor Manufacturing Limited

No. 1600, Zi Xing Road, Shanghai ZiZhu Science-based Industrial Park, 200241, China Tel: +86-21-24162266, Fax: +86-21-24162277

#### REGIONAL SALES OFFICE

Shenzhen Office

Shanghai SIM-BCD Semiconductor Manufacturing Co., Ltd., Shenzhen Office Room E, 5F, Noble Center, No.1006, 3rd Fuzhong Road, Futian District, Shenzhen, 518026, China Tel: +86-755-8826 7951

Tel: +86-755-8826 7951 Fax: +86-755-8826 7865 - Wafer Fab

Shanghai SIM-BCD Semiconductor Manufacturing Co., Ltd. 800 Yi Shan Road, Shanghai 200233, China Tel: +86-21-6485 1491, Fax: +86-21-5450 0008

Taiwan Office

BCD Semiconductor (Taiwan) Company Limited 4F, 298-1, Rui Guang Road, Nei-Hu District, Taipei,

Taiwan Tel: +886-2-2656 2808 Fax: +886-2-2656 2806 USA Office BCD Semiconductor Corp. 30920 Huntwood Ave. Hayward, CA 94544, USA Tel: +1-510-324-2988 Fax: +1-510-324-2788